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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	24KB (24K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21275sdfp-x6

Table 1.4 Product Information for R8C/27 Group

Current of Sep. 2008

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data flash				
R5F21272SNFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	
R5F21274SNFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SNXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	Factory programming product ⁽¹⁾
R5F21274SNXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		

NOTE:

1. The user ROM is programmed before shipment.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.

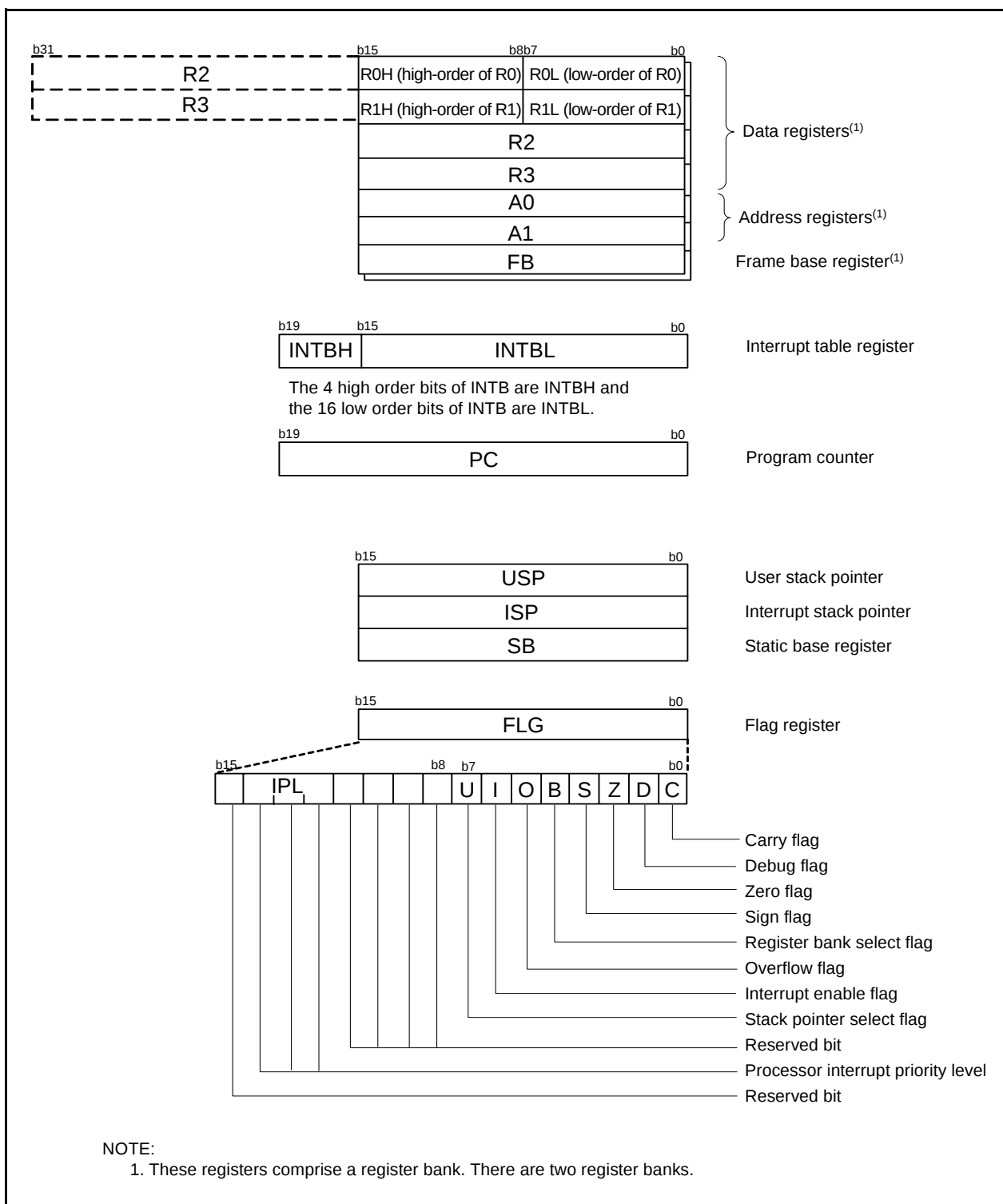


Figure 2.1 CPU Registers

3. Memory

3.1 R8C/26 Group

Figure 3.1 is a Memory Map of R8C/26 Group. The R8C/26 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.

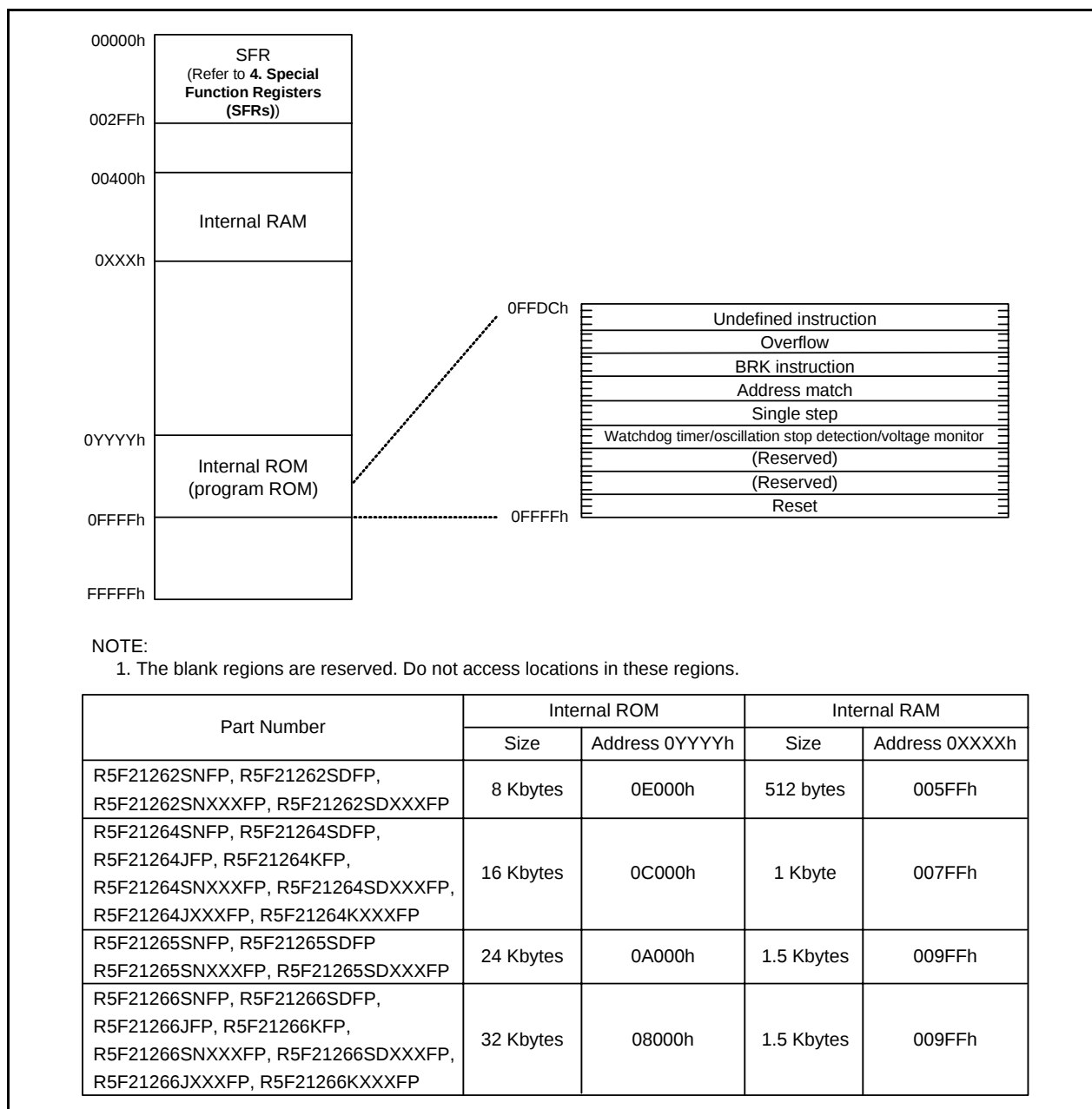


Figure 3.1 Memory Map of R8C/26 Group

Table 4.5 SFR Information (5)⁽¹⁾

Address	Register	Symbol	After reset
0100h	Timer RA Control Register	TRACR	00h
0101h	Timer RA I/O Control Register	TRAIOC	00h
0102h	Timer RA Mode Register	TRAMR	00h
0103h	Timer RA Prescaler Register	TRAPRE	FFh
0104h	Timer RA Register	TRA	FFh
0105h			
0106h	LIN Control Register	LINCR	00h
0107h	LIN Status Register	LINST	00h
0108h	Timer RB Control Register	TRBCR	00h
0109h	Timer RB One-Shot Control Register	TRBOCR	00h
010Ah	Timer RB I/O Control Register	TRBIOC	00h
010Bh	Timer RB Mode Register	TRBMR	00h
010Ch	Timer RB Prescaler Register	TRBPRE	FFh
010Dh	Timer RB Secondary Register	TRBSC	FFh
010Eh	Timer RB Primary Register	TRBPR	FFh
010Fh			
0110h			
0111h			
0112h			
0113h			
0114h			
0115h			
0116h			
0117h			
0118h	Timer RE Second Data Register / Counter Data Register	TRESEC	00h
0119h	Timer RE Minute Data Register / Compare Data Register	TREMIN	00h
011Ah	Timer RE Hour Data Register ⁽²⁾	TREHR	00h
011Bh	Timer RE Day of Week Data Register ⁽²⁾	TREWK	00h
011Ch	Timer RE Control Register 1	TRECR1	00h
011Dh	Timer RE Control Register 2	TRECR2	00h
011Eh	Timer RE Count Source Select Register	TRECSR	00001000b
011Fh			
0120h	Timer RC Mode Register	TRCMR	01001000b
0121h	Timer RC Control Register 1	TRCCR1	00h
0122h	Timer RC Interrupt Enable Register	TRCIER	01110000b
0123h	Timer RC Status Register	TRCSR	01110000b
0124h	Timer RC I/O Control Register 0	TRCIOR0	10001000b
0125h	Timer RC I/O Control Register 1	TRCIOR1	10001000b
0126h	Timer RC Counter	TRC	00h
0127h			00h
0128h	Timer RC General Register A	TRCGRA	FFh
0129h			FFh
012Ah	Timer RC General Register B	TRCGRB	FFh
012Bh			FFh
012Ch	Timer RC General Register C	TRCGRC	FFh
012Dh			FFh
012Eh	Timer RC General Register D	TRCGRD	FFh
012Fh			FFh
0130h	Timer RC Control Register 2	TRCCR2	00011111b
0131h	Timer RC Digital Filter Function Select Register	TRCDF	00h
0132h	Timer RC Output Master Enable Register	TRCOER	01111111b
0133h			
0134h			
0135h			
0136h			
0137h			
0138h			
0139h			
013Ah			
013Bh			
013Ch			
013Dh			
013Eh			
013Fh			

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. In J, K version these regions are reserved. Do not access locations in these regions.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽²⁾	R8C/26 Group	100 ⁽³⁾	–	–	times
		R8C/27 Group	1,000 ⁽³⁾	–	–	times
–	Byte program time		–	50	400	μs
–	Block erase time		–	0.4	9	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	μs
–	Interval from erase start/restart until following suspend request		650	–	–	μs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time ⁽⁷⁾	Ambient temperature = 55°C	20	–	–	year

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.13 Timing Requirements of Clock Synchronous Serial I/O with Chip Select⁽¹⁾

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
tsucyc	SSCK clock cycle time			4	–	–	tcyc ⁽²⁾
t _{HI}	SSCK clock "H" width			0.4	–	0.6	tsucyc
t _{LO}	SSCK clock "L" width			0.4	–	0.6	tsucyc
trise	SSCK clock rising time	Master		–	–	1	tcyc ⁽²⁾
		Slave		–	–	1	μs
tfall	SSCK clock falling time	Master		–	–	1	tcyc ⁽²⁾
		Slave		–	–	1	μs
tsu	SSO, SSI data input setup time			100	–	–	ns
t _H	SSO, SSI data input hold time			1	–	–	tcyc ⁽²⁾
t _{LEAD}	$\overline{\text{SCS}}$ setup time	Slave		1tcyc + 50	–	–	ns
t _{LAG}	$\overline{\text{SCS}}$ hold time	Slave		1tcyc + 50	–	–	ns
t _{OD}	SSO, SSI data output delay time			–	–	1	tcyc ⁽²⁾
t _{SA}	SSI slave access time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5tcyc + 100	ns
			2.2 V ≤ V _{CC} < 2.7 V	–	–	1.5tcyc + 200	ns
t _{OR}	SSI slave out open time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5tcyc + 100	ns
			2.2 V ≤ V _{CC} < 2.7 V	–	–	1.5tcyc + 200	ns

NOTES:

1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. 1tcyc = 1/f₁(s)

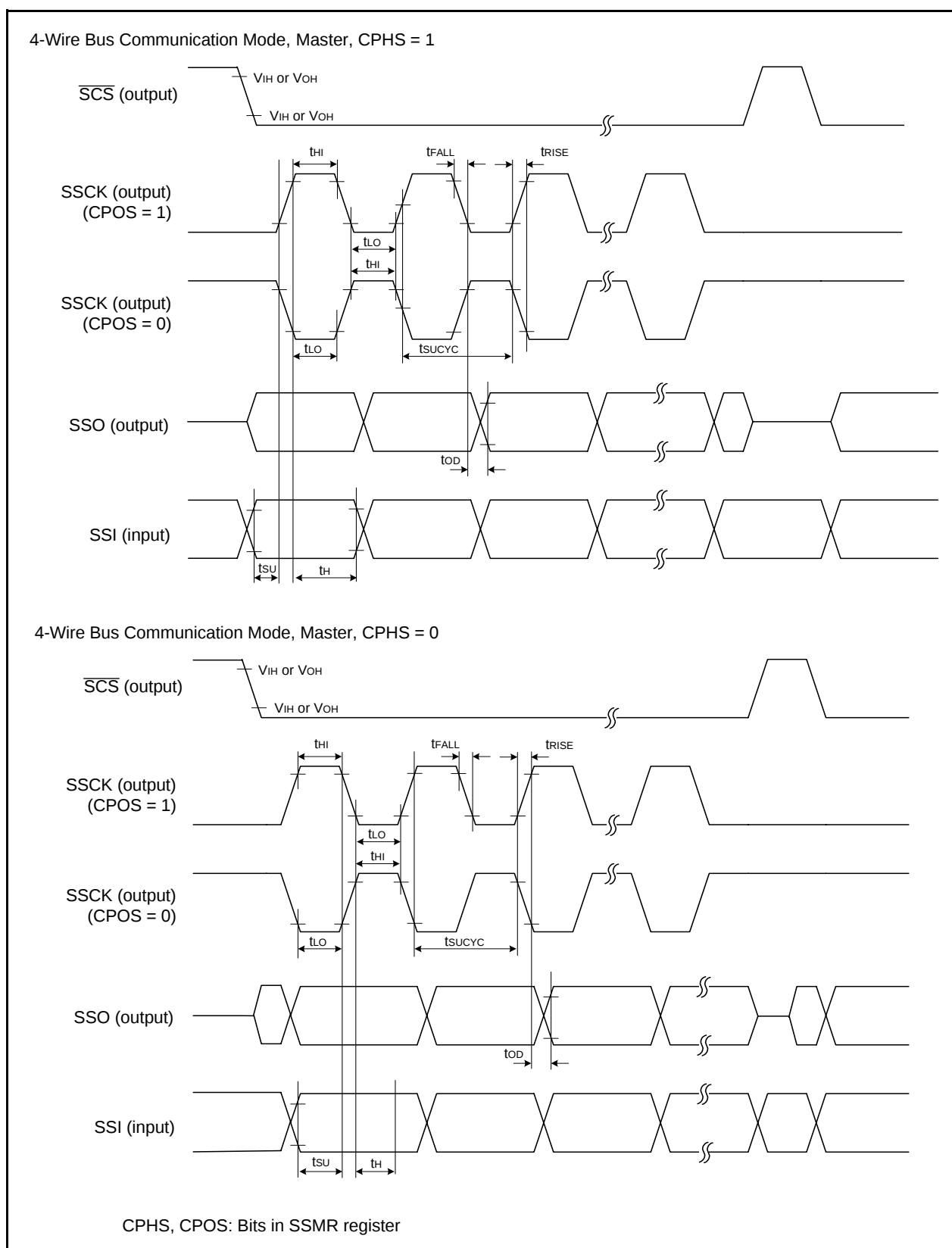


Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

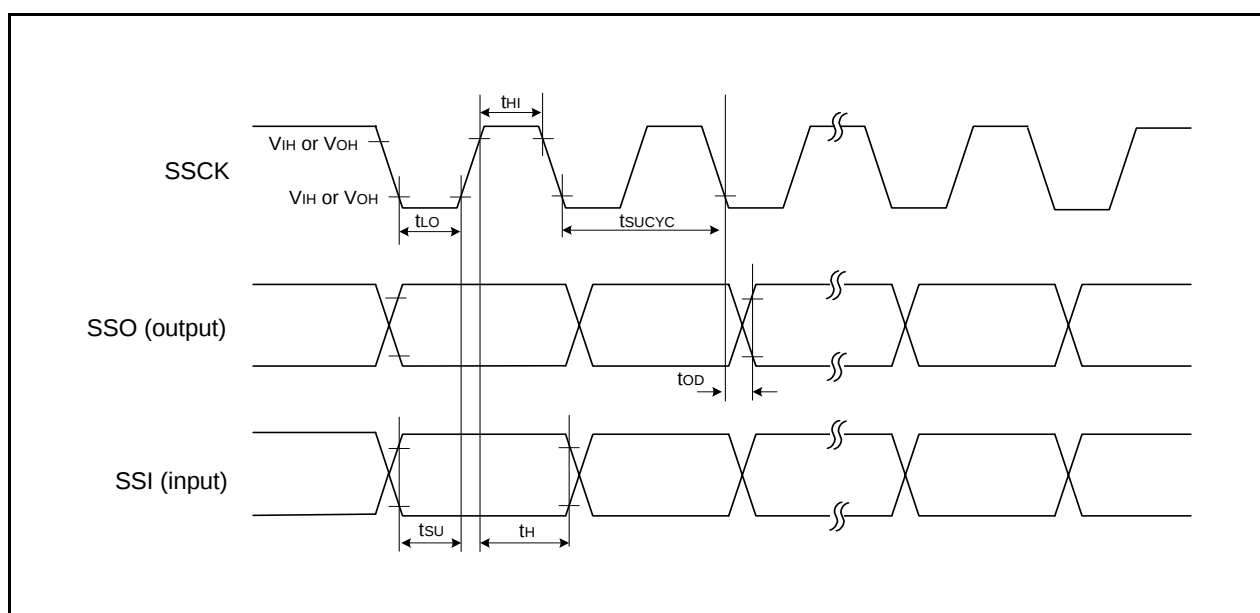


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.14 Timing Requirements of I²C bus Interface⁽¹⁾

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _{SCL}	SCL input cycle time		12t _{cy} + 600 ⁽²⁾	–	–	ns
t _{SCLH}	SCL input “H” width		3t _{cy} + 300 ⁽²⁾	–	–	ns
t _{SCLL}	SCL input “L” width		5t _{cy} + 500 ⁽²⁾	–	–	ns
t _{sf}	SCL, SDA input fall time		–	–	300	ns
t _{SP}	SCL, SDA input spike pulse rejection time		–	–	1t _{cy} ⁽²⁾	ns
t _{BUF}	SDA input bus-free time		5t _{cy} ⁽²⁾	–	–	ns
t _{STAH}	Start condition input hold time		3t _{cy} ⁽²⁾	–	–	ns
t _{STAS}	Retransmit start condition input setup time		3t _{cy} ⁽²⁾	–	–	ns
t _{STOP}	Stop condition input setup time		3t _{cy} ⁽²⁾	–	–	ns
t _{SDAS}	Data input setup time		1t _{cy} + 20 ⁽²⁾	–	–	ns
t _{SDAH}	Data input hold time		0	–	–	ns

NOTES:

1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. 1t_{cy} = 1/f₁(s)

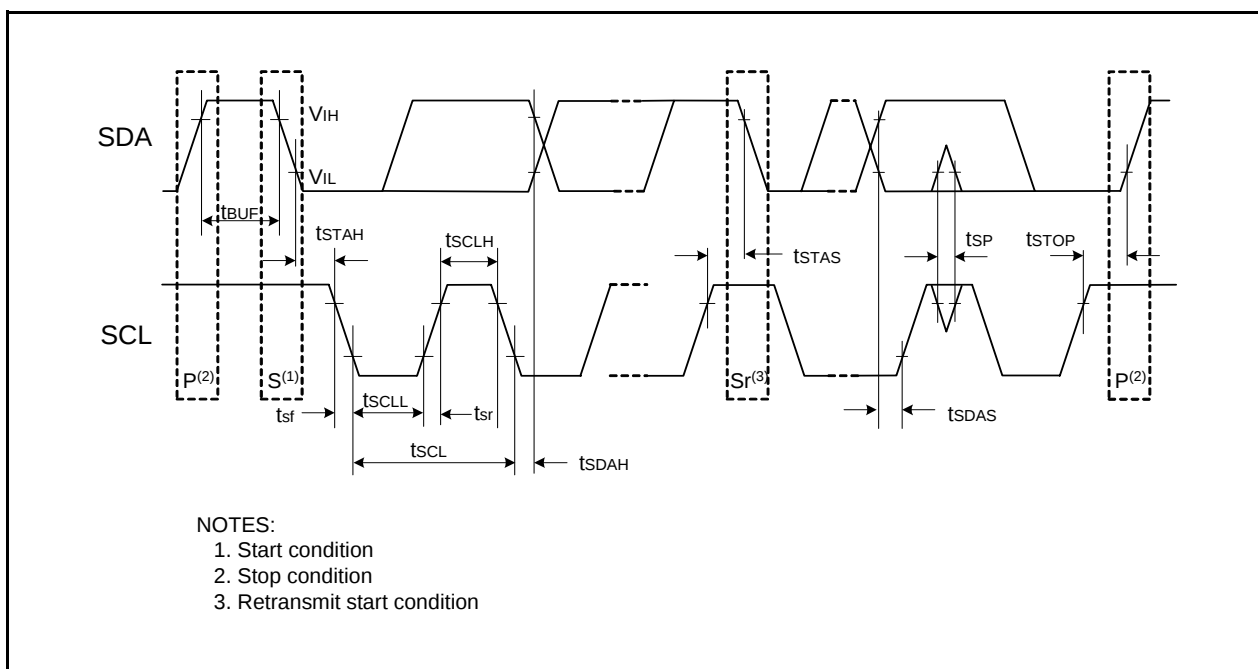
**Figure 5.7 I/O Timing of I²C bus Interface**

Table 5.15 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V _{OH}	Output "H" voltage	Except P1_0 to P1_7, XOUT	I _{OH} = -5 mA		V _{CC} - 2.0	—	V _{CC}	V
			I _{OH} = -200 μA		V _{CC} - 0.5	—	V _{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I _{OH} = -20 mA	V _{CC} - 2.0	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -5 mA	V _{CC} - 2.0	—	V _{CC}	V
		XOUT	Drive capacity HIGH	I _{OH} = -1 mA	V _{CC} - 2.0	—	V _{CC}	V
			Drive capacity LOW	I _{OH} = -500 μA	V _{CC} - 2.0	—	V _{CC}	V
V _{OL}	Output "L" voltage	Except P1_0 to P1_7, XOUT	I _{OL} = 5 mA		—	—	2.0	V
			I _{OL} = 200 μA		—	—	0.45	V
		P1_0 to P1_7	Drive capacity HIGH	I _{OL} = 20 mA	—	—	2.0	V
			Drive capacity LOW	I _{OL} = 5 mA	—	—	2.0	V
		XOUT	Drive capacity HIGH	I _{OL} = 1 mA	—	—	2.0	V
			Drive capacity LOW	I _{OL} = 500 μA	—	—	2.0	V
V _{T+} -V _{T-}	Hysteresis	INT0, INT1, INT3, KI0, KI1, KI2, KI3, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	—	V
		RESET			0.1	1.0	—	V
I _{IH}	Input "H" current		V _I = 5 V, V _{CC} = 5 V		—	—	5.0	μA
I _{IL}	Input "L" current		V _I = 0 V, V _{CC} = 5 V		—	—	-5.0	μA
R _{PULLUP}	Pull-up resistance		V _I = 0 V, V _{CC} = 5 V		30	50	167	kΩ
R _{FXIN}	Feedback resistance	XIN			—	1.0	—	MΩ
R _{FXCIN}	Feedback resistance	XCIN			—	18	—	MΩ
V _{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

NOTE:

- V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

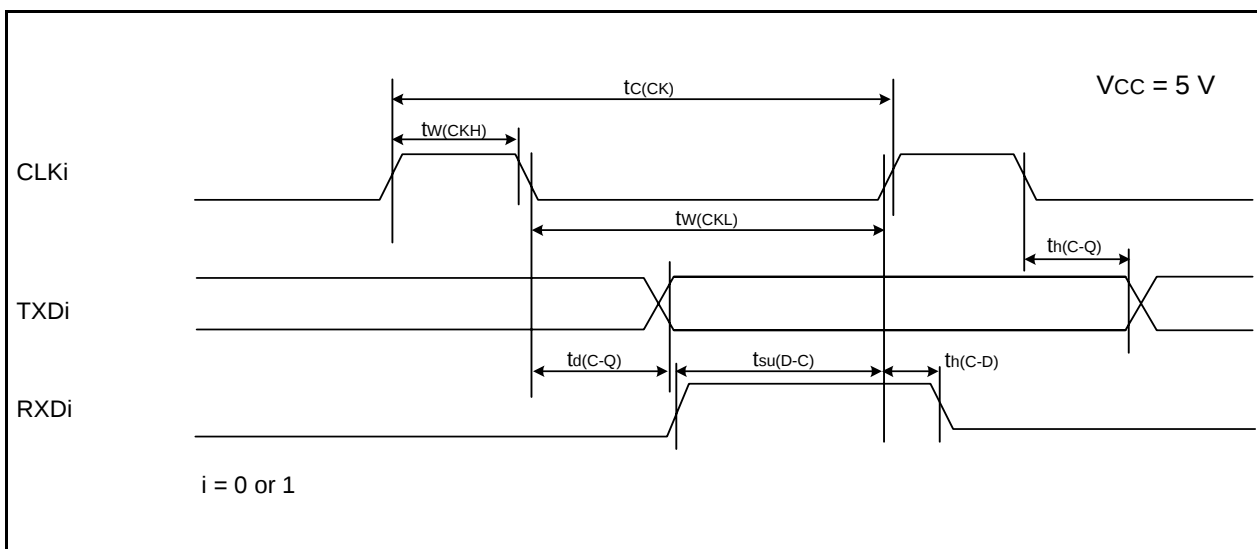
Table 5.17 Electrical Characteristics (3) [V_{CC} = 5 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit	
			Min.	Typ.	Max.		
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	75	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	60	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	4.0	–	μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.2	–	μA
		Stop mode	XIN clock off, Topr = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.8	3.0	μA
			XIN clock off, Topr = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.2	–	μA

Table 5.20 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{w(CKH)}$	CLKi input "H" width	100	—	ns
$t_{w(CKL)}$	CLKi input "L" width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 or 1

**Figure 5.10 Serial Interface Timing Diagram when Vcc = 5 V****Table 5.21 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width	250 ⁽¹⁾	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width	250 ⁽²⁾	—	ns

NOTES:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

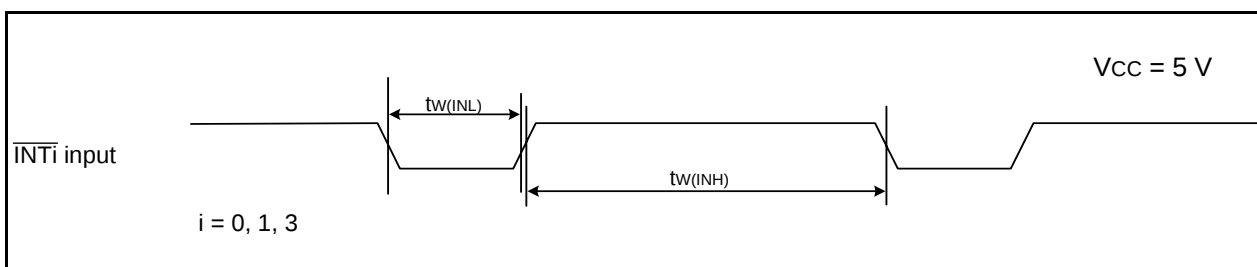
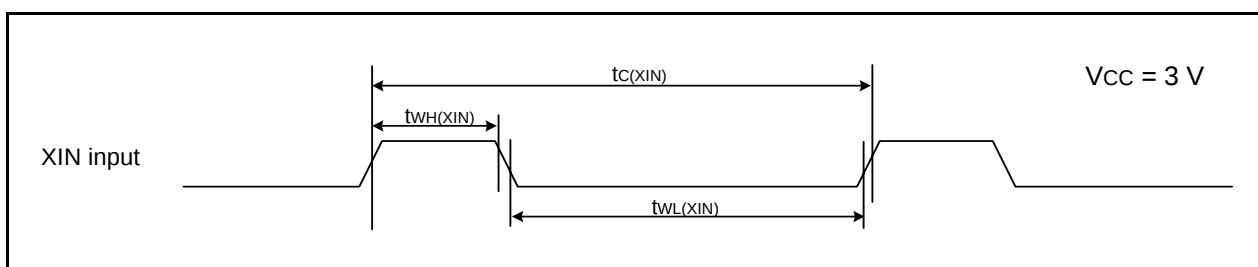
**Figure 5.11 External Interrupt $\overline{INTi}$ Input Timing Diagram when Vcc = 5 V**

Table 5.23 Electrical Characteristics (4) [V_{CC} = 3 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
I _{CC}	Power supply current (V _{CC} = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V _{SS}	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on f _{OCO} = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN clock off High-speed on-chip oscillator on f _{OCO} = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1			μA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1			μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off, T _{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA
		Stop mode	XIN clock off, T _{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA

Timing requirements**(Unless Otherwise Specified: $V_{CC} = 3\text{ V}$, $V_{SS} = 0\text{ V}$ at $T_{opr} = 25^{\circ}\text{C}$) [$V_{CC} = 3\text{ V}$]****Table 5.24 XIN Input, XCIN Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	100	–	ns
$t_{WH(XIN)}$	XIN input “H” width	40	–	ns
$t_{WL(XIN)}$	XIN input “L” width	40	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	–	μs
$t_{WH(XCIN)}$	XCIN input “H” width	7	–	μs
$t_{WL(XCIN)}$	XCIN input “L” width	7	–	μs

**Figure 5.12 XIN Input and XCIN Input Timing Diagram when $V_{CC} = 3\text{ V}$** **Table 5.25 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	–	ns

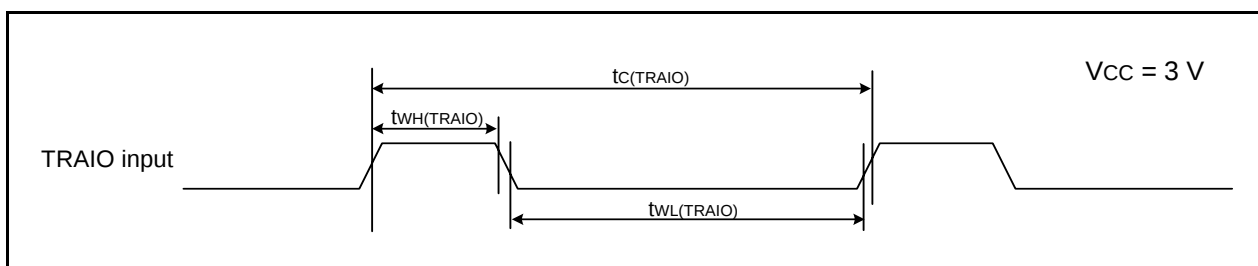
**Figure 5.13 TRAIO Input Timing Diagram when $V_{CC} = 3\text{ V}$**

Table 5.38 Flash Memory (Data flash Block A, Block B) Electrical Characteristics⁽⁴⁾

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽²⁾		10,000 ⁽³⁾	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	50	400	μs
—	Byte program time (program/erase endurance > 1,000 times)		—	65	—	μs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	9	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	97 + CPU clock × 6 cycles	μs
—	Interval from erase start/restart until following suspend request		650	—	—	μs
—	Interval from program start/restart until following suspend request		0	—	—	ns
—	Time from suspend until program/erase restart		—	—	3 + CPU clock × 4 cycles	μs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		2.7	—	5.5	V
—	Program, erase temperature		-40	—	85 ⁽⁸⁾	°C
—	Data hold time ⁽⁹⁾	Ambient temperature = 55°C	20	—	—	year

NOTES:

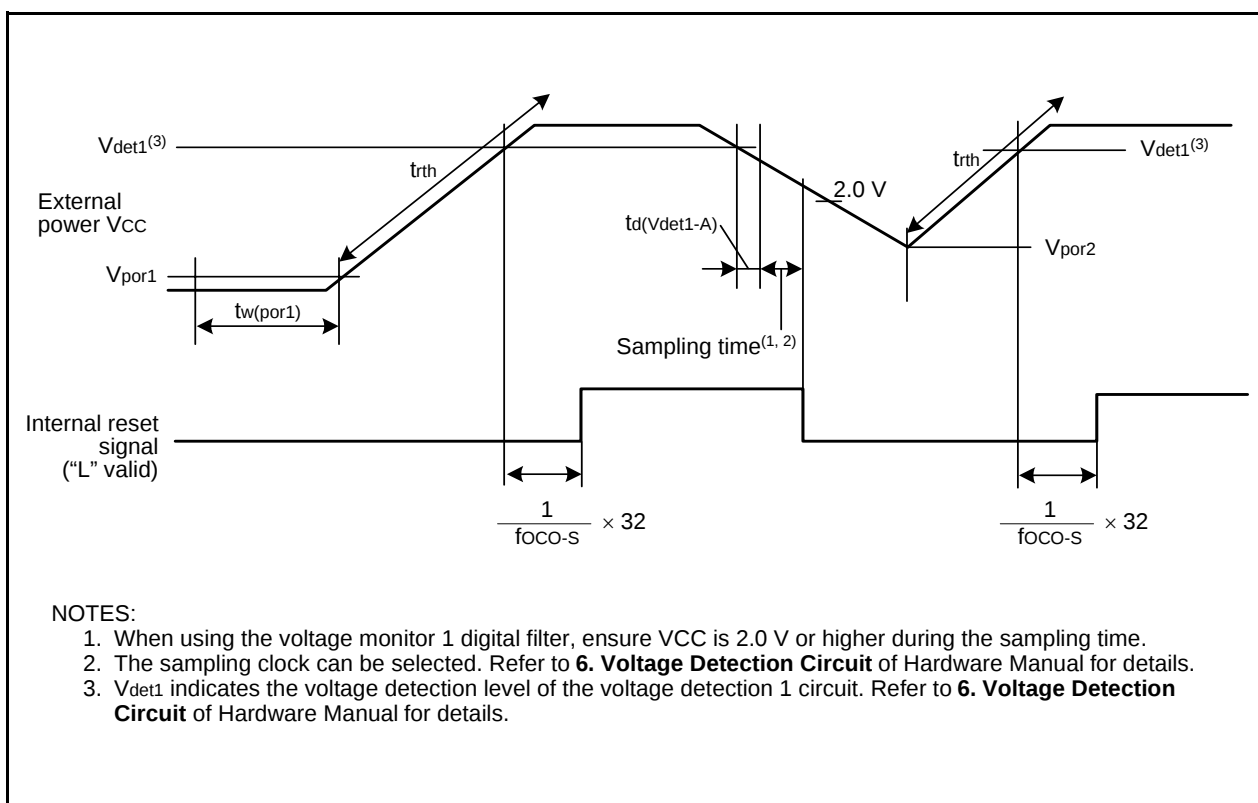
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. 125°C for K version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.41 Power-on Reset Circuit, Voltage Monitor 1 Reset Electrical Characteristics⁽³⁾

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{por1}	Power-on reset valid voltage ⁽⁴⁾		–	–	0.1	V
V _{por2}	Power-on reset or voltage monitor 1 reset valid voltage		0	–	V _{det1}	V
tr _{th}	External power V _{cc} rise gradient	V _{cc} ≤ 3.6 V	20 ⁽²⁾	–	–	mV/msec
		V _{cc} > 3.6 V	20 ⁽²⁾	–	2,000	mV/msec

NOTES:

1. The measurement condition is T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. This condition (the minimum value of external power V_{cc} rise gradient) does not apply if V_{por2} ≥ 1.0 V.
3. To use the power-on reset function, enable voltage monitor 1 reset by setting the LVD1ON bit in the OFS register to 0, the VW1C0 and VW1C6 bits in the VW1C register to 1 respectively, and the VCA26 bit in the VCA2 register to 1.
4. tw_(por1) indicates the duration the external power V_{cc} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain tw_(por1) for 30 s or more if -20°C ≤ T_{opr} ≤ 125°C, maintain tw_(por1) for 3,000 s or more if -40°C ≤ T_{opr} < -20°C.

**Figure 5.22 Reset Circuit Electrical Characteristics**

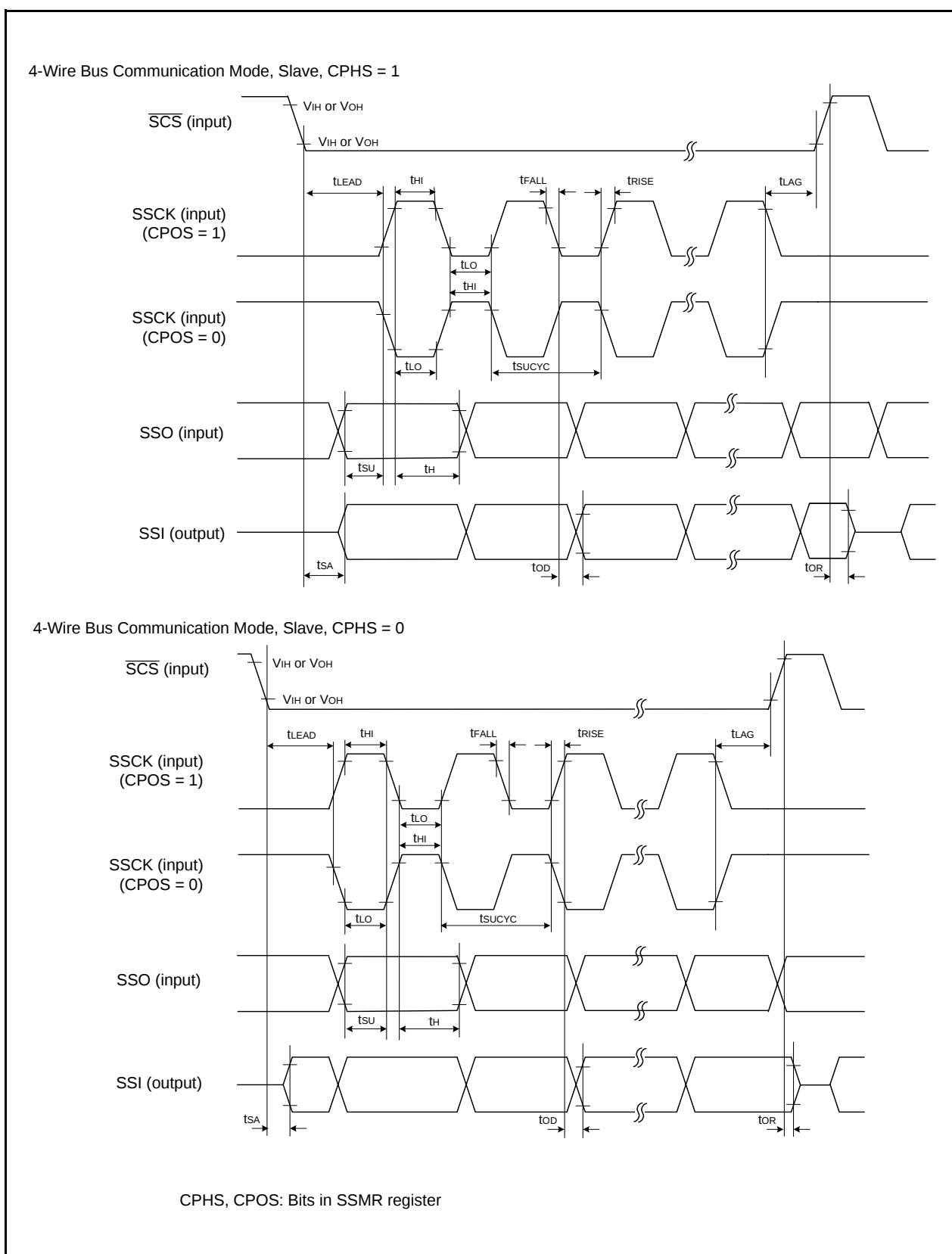
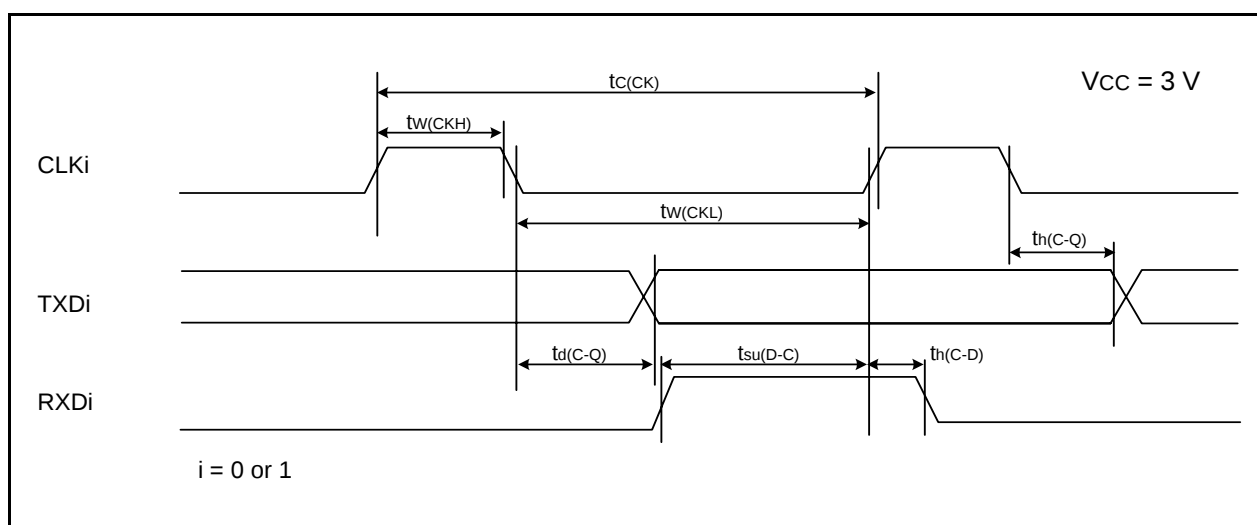


Figure 5.24 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

Table 5.57 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	—	ns
$t_{w(CKH)}$	CLKi input "H" width	150	—	ns
$t_{w(CKL)}$	CLKi Input "L" width	150	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	70	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

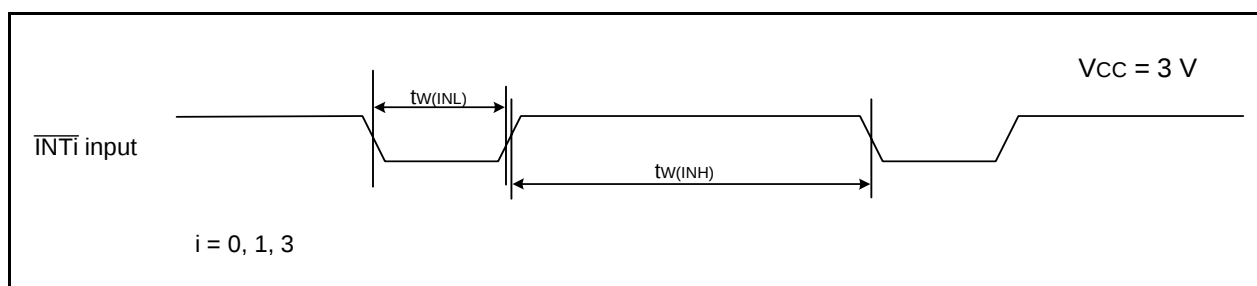
i = 0 or 1

**Figure 5.33 Serial Interface Timing Diagram when Vcc = 3 V****Table 5.58 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width	380 ⁽¹⁾	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width	380 ⁽²⁾	—	ns

NOTES:

1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

**Figure 5.34 External Interrupt $\overline{INTi}$ Input Timing Diagram when Vcc = 3 V**

REVISION HISTORY	R8C/26 Group, R8C/27 Group Datasheet
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Rev.	Date	Description	
		Page	Summary
0.10	Nov 14, 2005	–	First edition issued
0.20	Feb 06, 2006	2, 3	Table 1.1 Functions and Specifications for R8C/26Group and Table 1.2 Functions and Specifications for R8C/27 Group; Minimum instruction execution time and Supply voltage revised
		9	Table 1.6 Pin Name Information by Pin Number; “XOUT” → “XOUT/XCOUT” and “XIN” → “XIN/XCIN” revised
		18	Table 4.4 SFR Information (4); 00FEh: “DRR” → “P1DRR” revised
		19	Table 4.5 SFR Information (5); -0119h: “Timer RE Minute Data Register / Compare Register” → “Timer RE Minute Data Register / Compare Data Register” -011Ah: “Timer RE Time Data Register” → “Timer RE Hour Data Register” -011Bh: “Timer RE Day Data Register” → “Timer RE Day of Week Data Register” revised
		22 to 45	5. Electrical Characteristics added
1.00	Nov 08, 2006	All pages	“Preliminary” deleted
		2	Table 1.1 revised
		3	Table 1.2 revised
		4	Figure 1.1 revised
		5	Table 1.3 revised
		6	Table 1.4 revised
		7	Figure 1.4 revised
		9	Table 1.6 revised
		15	Table 4.1; • 001Ch: “00h” → “00h, 10000000b” revised • 000Fh: “000XXXXXb” → “00X11111b” revised • 0029h: “High-Speed On-Chip Oscillator Control Register 4, FRA4, When shipping” added • 002Bh: “High-Speed On-Chip Oscillator Control Register 6, FRA6, When shipping” added • 0032h: “00h, 01000000b” → “00h, 00100000b” revised • 0038h: “00001000b, 01001001b” → “0000X000b, 0100X001b” revised • NOTE3 and 4 revised; NOTE6 added
		18	Table 4.4; • 00E0h, 00E1h, 00E5h, 00E8h, 00E9h: “XXh” → “00h” revised • 00FDh: “XX00000000b” → “00h” revised
		22	Table 5.2 revised
		23	Figure 5.1 title revised
		24	Table 5.4 revised
		25	Table 5.5 revised
		26	Figure 5.2 title revised and Table 5.7 NOTE4 added

REVISION HISTORY

R8C/26 Group, R8C/27 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.30	May 25, 2007	16	Figure 3.2 part number revised
		30	Table 5.10 revised
		53	Table 5.39 NOTE4 added
		55	Table 5.42 revised
1.40a	Jun 14, 2007	5, 7	Table 1.3 and Table 1.4 revised
2.00	Mar 01, 2008	1, 49	1.1, 5.2 "J and K versions are ..." deleted
		5, 7	Table 1.3, Table 1.4 revised
		11	Table 1.6 NOTE3 added
		15, 16	Figure 3.1, Figure 3.2; "Expanded area" deleted
		17	Table 4.1 "002Ch" added
		18	Table 4.2 "0036h"; J, K version "0100X000b" → "0100X001b"
		24, 49	Table 5.2, Table 5.35; NOTE2 revised
2.10	Sep 26, 2008	30	Table 5.10 revised, NOTE4 added
		–	"RENESAS TECHNICAL UP DATE" reflected: TN-16C-A172A/E
		26, 51	Table 5.4, Table 5.37 NOTE2, NOTE4 revised
		27, 52	Table 5.5, Table 5.38 NOTE2, NOTE5 revised
		53	Table 5.39 Parameter: Voltage monitor 1 reset generation time added NOTE5 added
			Table 5.40 revised
		54	Table 5.41 revised
			Figure 5.22 revised

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